

N-channel Power MOSFET:
30V, 2.5mohm, 70A

Product Summary

VDSS	VGSS	RDS(ON) TYP/MAX	ID MAX
30V	± 20V	2.5/3.3 mΩ@VGS=10V 4.0/7.3 mΩ@VGS=4.5V	70A

Marking Symbol Code

- ❖ Laser Marking Device Code: AEM



GS : Gostone (fixed)
AEM: Marking Device Code (fixed)
A: Factory Code
Y: Year Code
WW: Week Code
LT: LOT Code
o : Pin#1 Identifier

Form

- ❖ Tape & Reel Embossed Type: 5,000pcs / reel

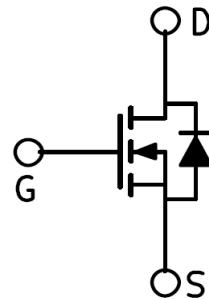
Features

- ❖ Low RDSon
- ❖ Low Gate Charge
- ❖ High Current Capacity
- ❖ Halogen-Free / RoHS Compliant

Application

- ❖ Battery Charging & Discharging for NB Battery Pack
- ❖ DC/DC Converters in Computing.

Equivalent circuit



Absolute Maximum Rating Ta=25°C

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	30	V
Gate to Source Voltage	VGS	±20	V
Continuous Drain Current	IDS	70	A
		44	A
Pulsed Drain Current*1	IDM	140	A
Continuous Drain Current	IDS	18	A
		15	A
Avalanche Current	IAS	24	A
Avalanche Energy	EAS	28.5	mJ
Power Dissipation	PD	33	W
		13	W
Power Dissipation*3	PDSM	5.0	W
		3.2	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

*1Pulse width limited by maximum junction temperature.

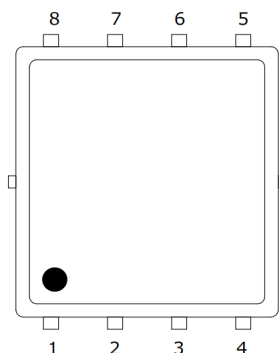
*2The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

*3The Power dissipation is based on R_{θJA} t ≤ 10s value.

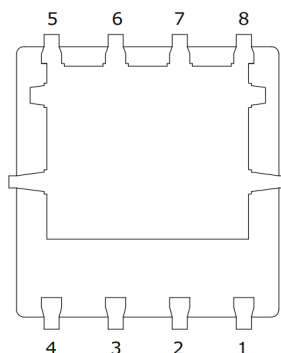
Thermal Characteristics (Typical)

Parameter	Symbol	Rating	Unit
Junction-to Ambient (T _A =25°C)			
t ≤ 10s	R _{thJA} ^{*2}	20	°C/W
Steady-State		50	°C/W
Junction-to Case (T _C =25°C)			
Steady-State	R _{thJC}	2.9	°C/W

Top View



Bottom View



1,2,3: Source
4: Gate
5,6,7,8: Drain



Electrical Characteristics (Tj=25degC)

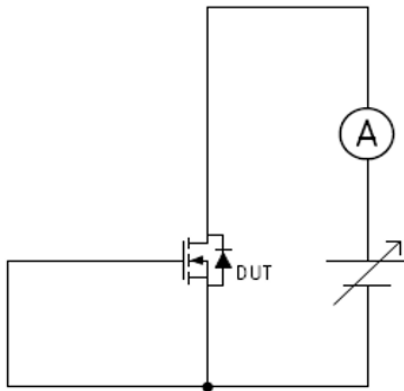
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID=250μA, VGS=0V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS=24V, VGS=0V			1	μA
Gate-Source Leakage Current	IGSS	VGS=±20V, VDS=0V			±100	nA
Gate-Source Threshold Voltage	Vth	VDS=VGS, ID=250μA	1.2	1.7	2.4	V
Drain-Source On-State Resistance	RDS(on)1 RDS(on)2	ID=13A, VGS=10V ID=13A, VGS=4.5V		2.5 4.0	3.3 7.3	mΩ
Forward Transconductance	gFS	VGS=5V, ID=13A		59		S
Input Capacitance *1	Ciss	VDS=15V, VGS=0V, f=1MHz		1,144		pF
Output Capacitance *1	Coss			900		
Reverse Transfer Capacitance *1	Crss			40		
Gate Resistance *1	Rg	f=1MHz		3.2		Ω
Turn-On Delay Time *1 *2	td(on)	VDD=15V, VGS=10V, ID=13A		7		ns
Rise Time *1 *2	tr			10		
Turn-Off Delay Time *1 *2	td(off)	VDD=15V, VGS=10V, ID=13A		31		ns
Fall Time *1 *2	tf			12		
Total Gate Charge *1	Qg	VDD=15V, VGS=10V, ID=13A		18.2		nC
Gate-Source Charge *1	Qgs			3.5		
Gate-Drain Charge *1	Qgd			3.1		
Diode Forward Voltage	VSD	IS=13A, VGS=0V			1.2	V
Maximum Body Diode Continuous Current	IS				26	A
Body Diode Reverse Recovery Time *1	trr	IF=13A, di/dt=100A/μs		19.0		ns
Body Diode Reverse Recovery Charge *1	Qrr			7.7		nC

Note *1 Guaranteed by Design

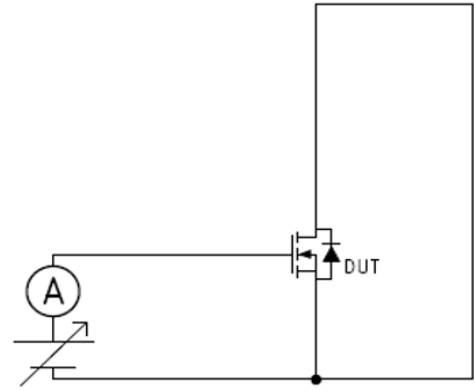
Note *2 Measurement Circuit for Switching Characteristics

Test circuits

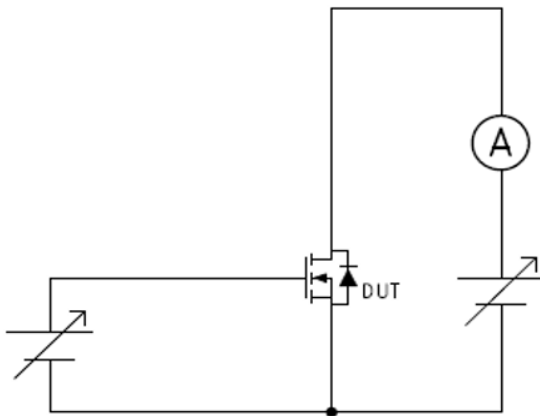
Test Circuit 1
VDSS/IDSS



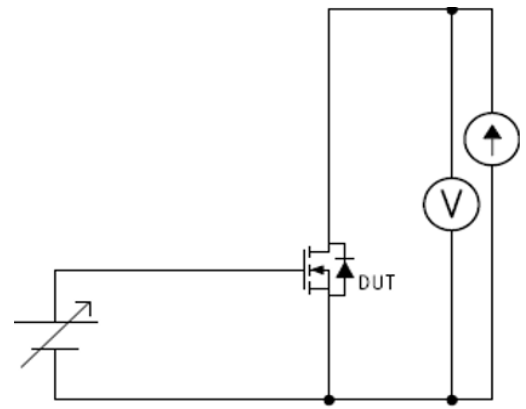
Test Circuit 2
IGSS



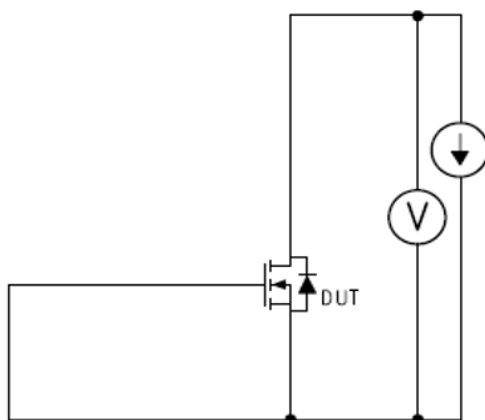
Test Circuit 3
Vth



Test Circuit 4
RDS(on)

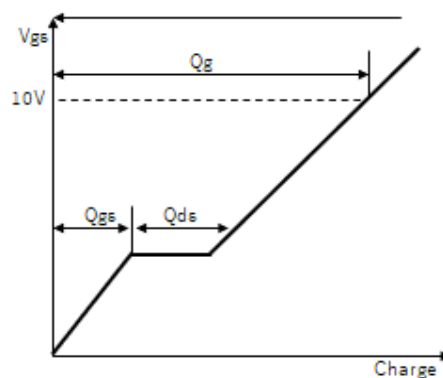
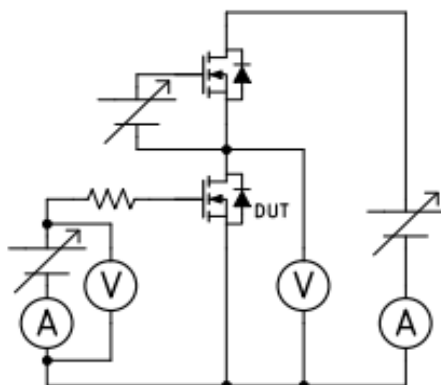


Test Circuit 5
VF

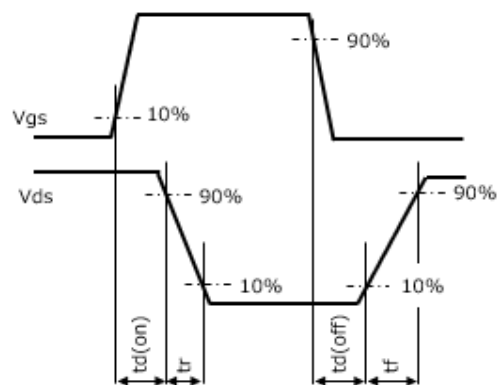
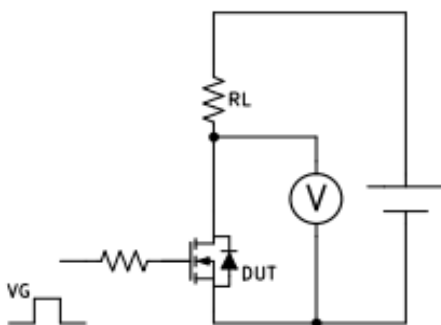


Test circuits

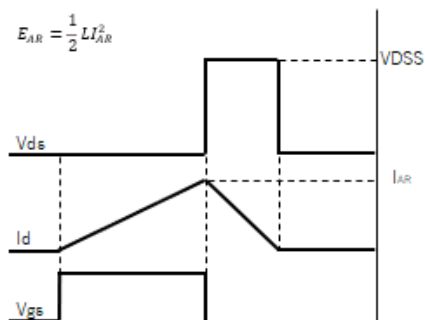
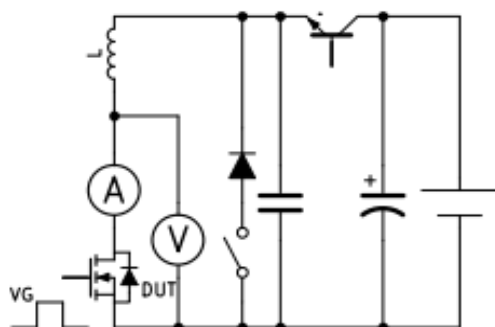
Test Circuit 6
Q_g



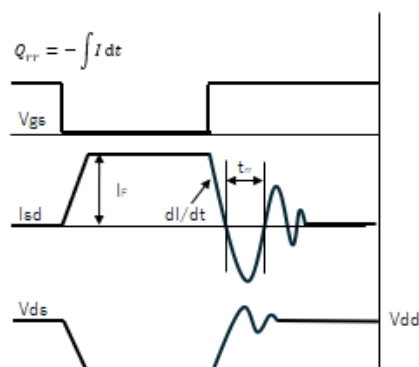
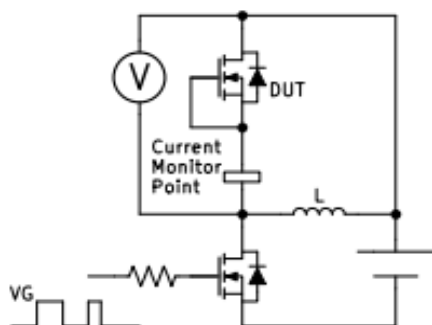
Test Circuit 7
Switching Time

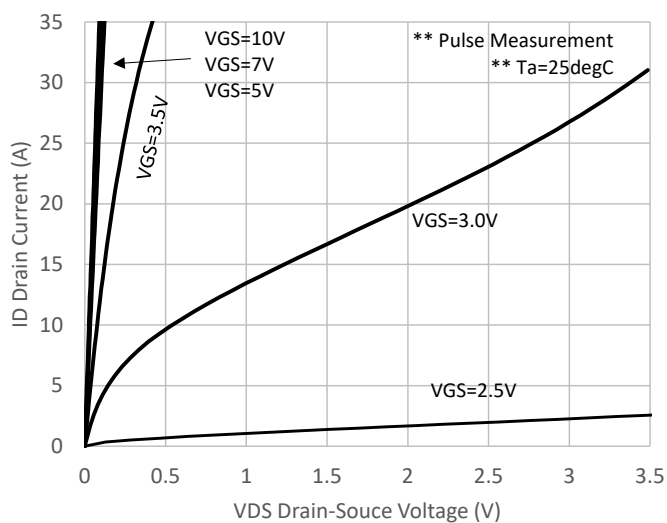
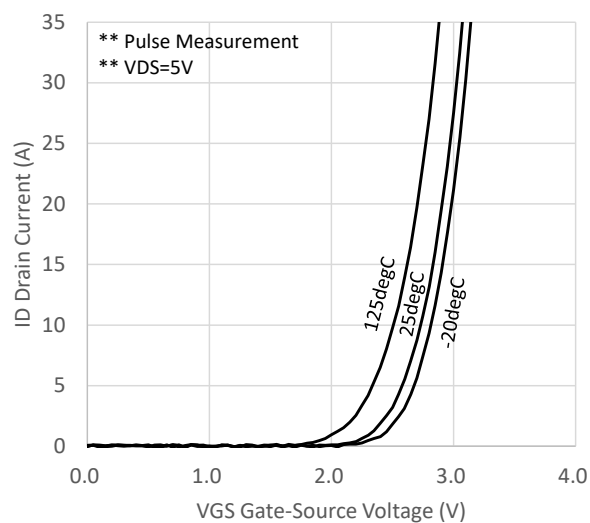
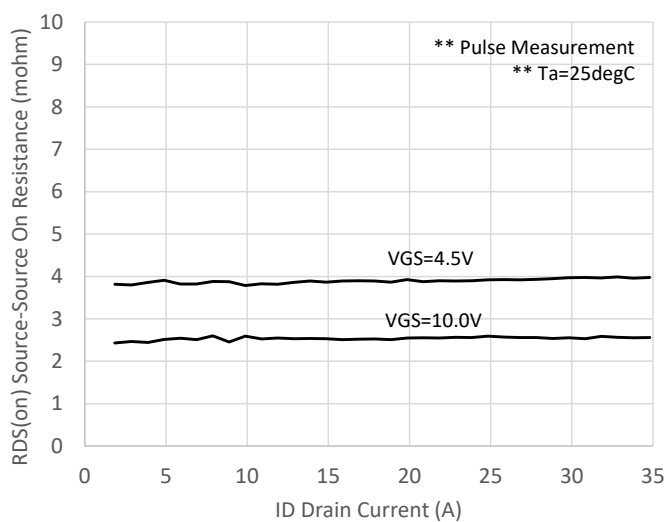
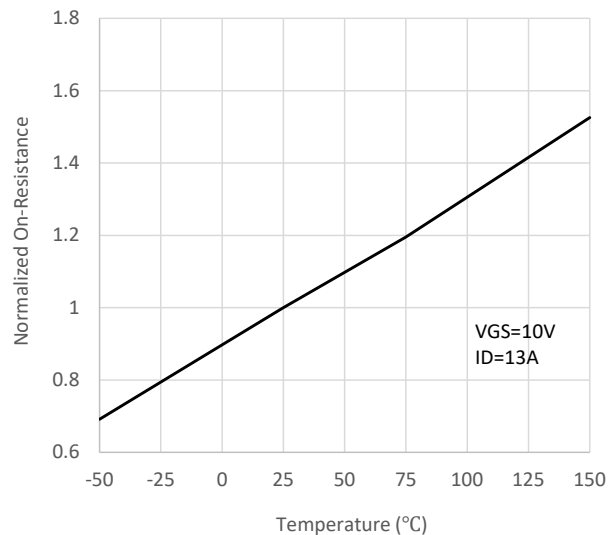
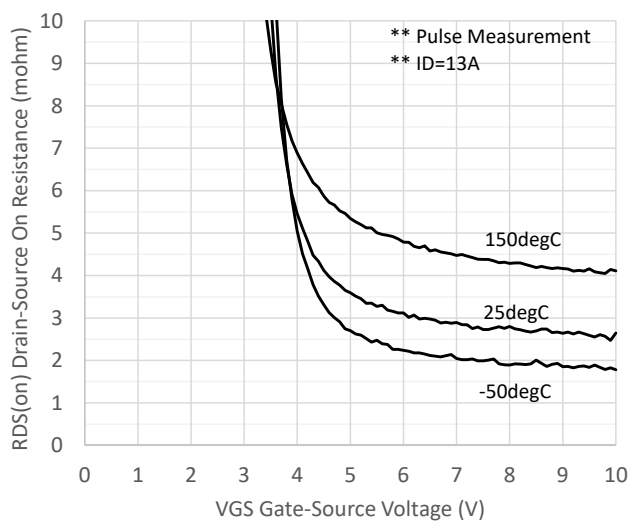
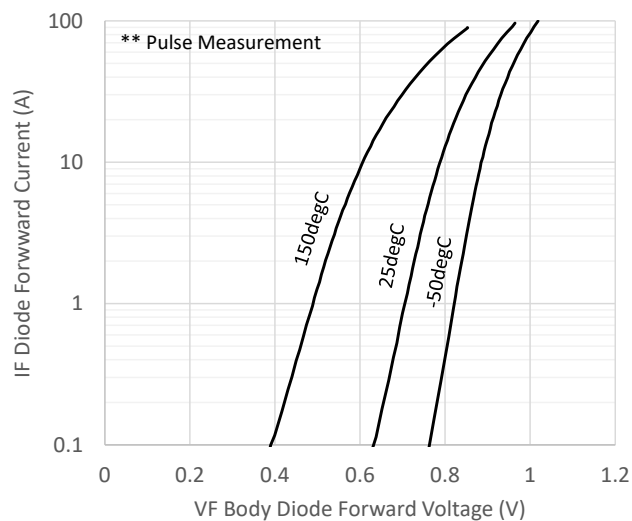


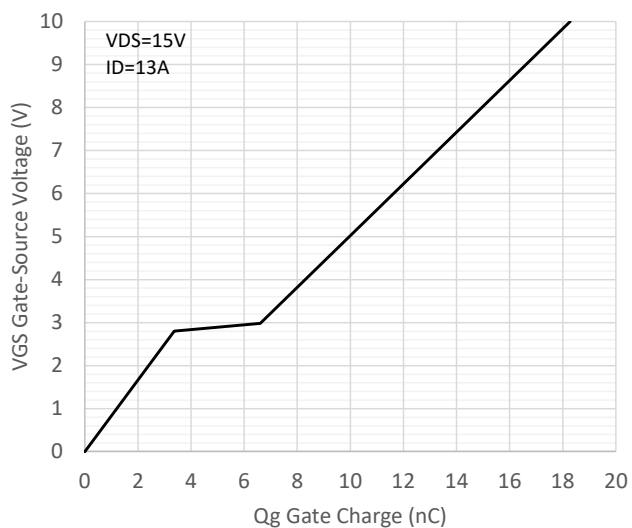
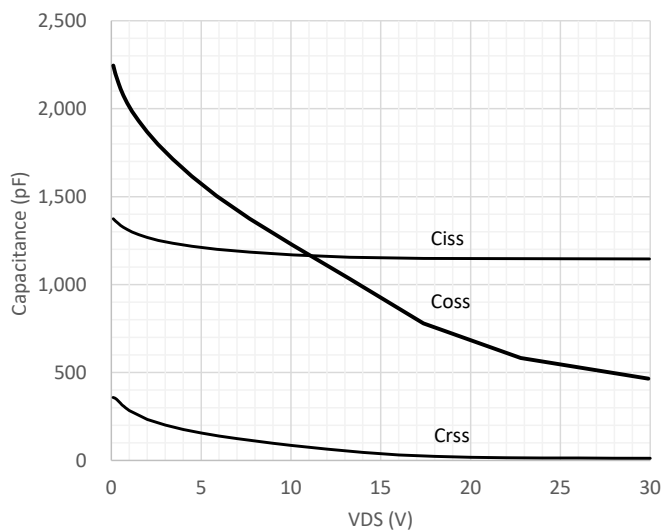
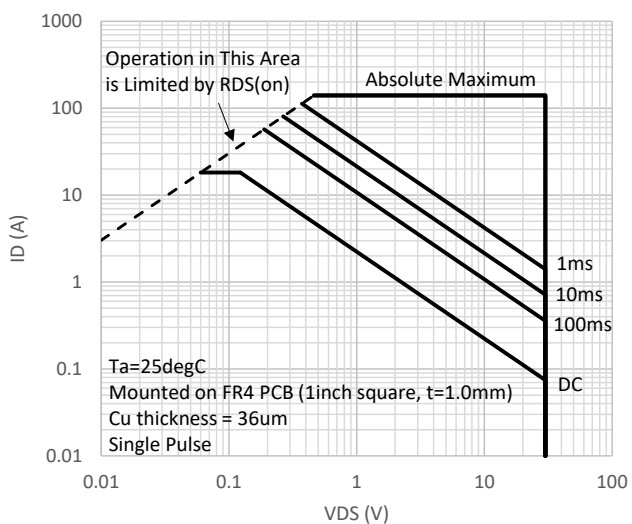
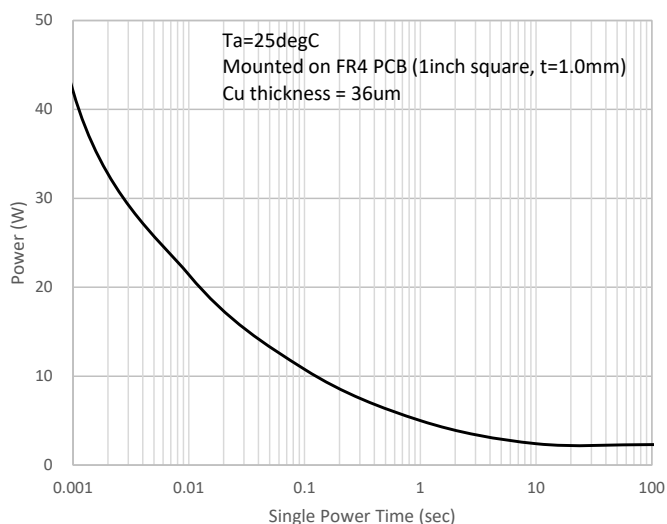
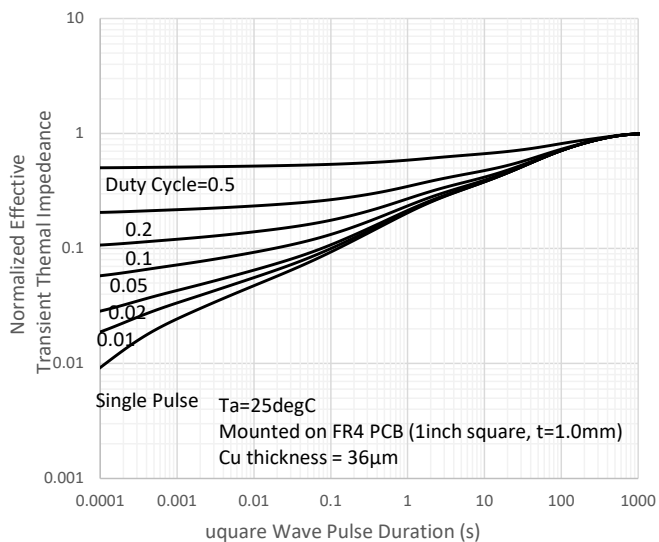
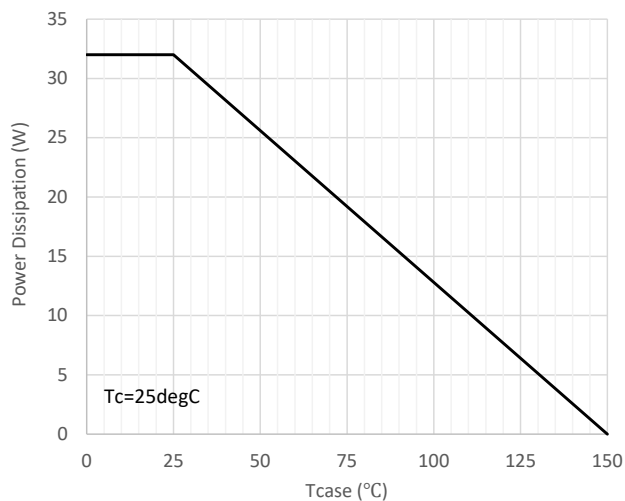
Test Circuit 8
IAS



Test Circuit 9
trr/Qrr

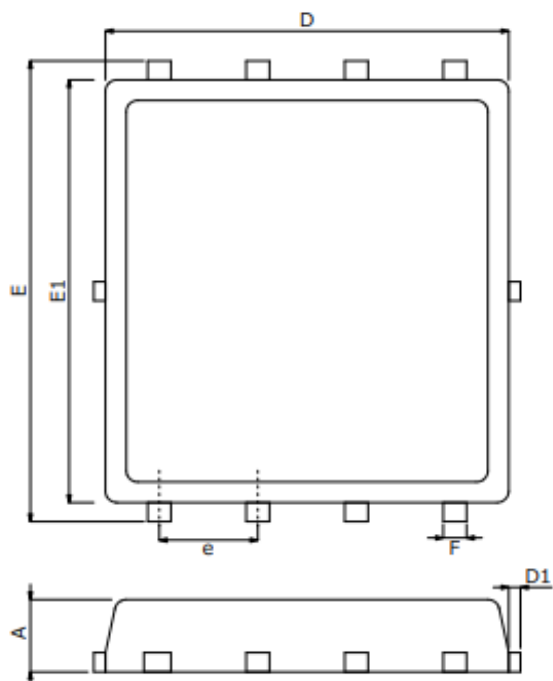


Technical data
ID to VDS

ID to VGS

RDS(on) to ID

On-Resistance vs Junction Temperature

RDS(on) to VGS

IF to VF


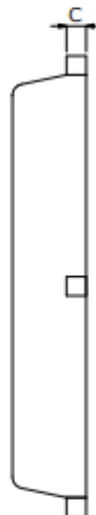
Technical data
Gate-Charge Characteristics

Capacitance Characteristic

SOA

Single Pulse Maximum Power Dissipation

Thermal Response

Power Derating


Package Outline Dimensions

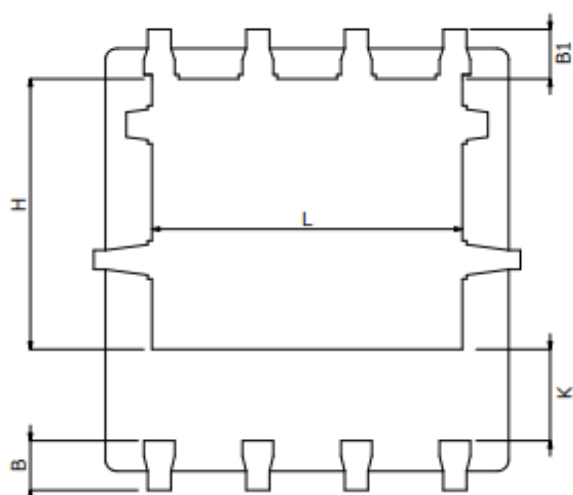
Top View



Side View



Bottom View

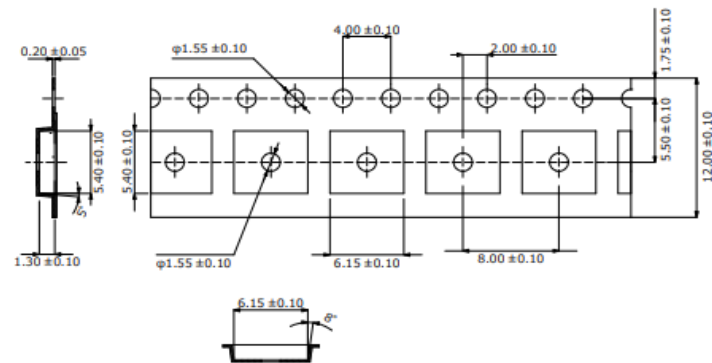


Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	0.900	0.950	1.000
B	0.480	0.580	0.680
B1	0.550	0.650	0.750
C	0.200	0.254	0.300
D	5.100	5.200	5.300
D1	-	-	0.150
E	5.900	6.050	6.200
E1	5.400	5.550	5.700
e	1.220	1.270	1.320
F	0.250	0.300	0.350
H	3.270	3.470	3.670
L	3.800	4.000	4.200
K	1.200	-	-

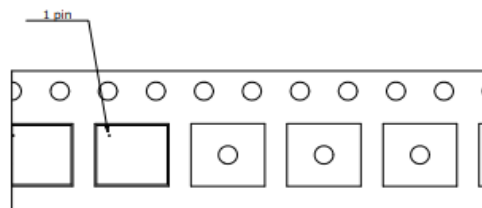
Form

- ❖ Tape & Reel Embossed Type: 5,000pcs / reel
- ❖ Factory PKG Code: PDFN
- ❖ Tape Width: 12mm, Pitch: 8mm, Reel Size: 12inch

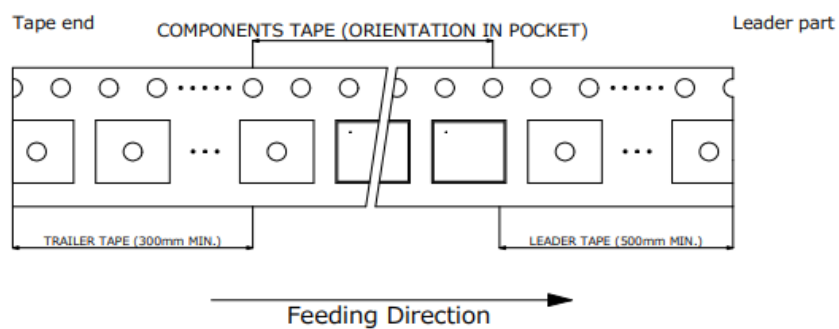
Tape size (mm)



Pin1 Direction



Tape end ~ Leader part (mm)



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